NTR2101P

Small Signal MOSFET

−8.0 V, −3.7 A, Single P−Channel, SOT−23

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
−8.0 V	39 mΩ @ −4.5 V	−3.7 A
	52 mΩ @ −2.5 V	
	79 mΩ @ −1.8 V	

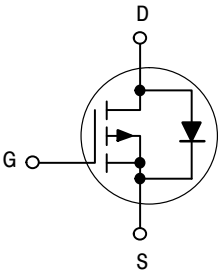
Features

- Leading Trench Technology for Low $R_{DS(on)}$
- −1.8 V Rated for Low Voltage Gate Drive
- SOT−23 Surface Mount for Small Footprint (3 x 3 mm)
- This is a Pb−Free Device

Applications

- High Side Load Switch
- DC−DC Conversion
- Cell Phone, Notebook, PDAs, etc.

P−Channel



MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

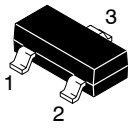
Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	−8.0	V
Gate−to−Source Voltage			V_{GS}	±8.0	V
Continuous Drain Current (Note 1)	t ≤ 5 s	T_A = 25°C	I_D	−3.7	A
		T_A = 70°C		−3.0	
Power Dissipation (Note 1)	t ≤ 5 s		P_D	0.96	W
Pulsed Drain Current	t_p = 10 μs		I_{DM}	−11	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	−1.2	A
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction−to−Ambient − Steady State	$R_{\theta JA}$	160	°C/W
Junction−to−Ambient − t ≤ 5 s	$R_{\theta JA}$	130	

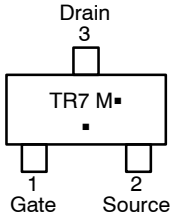
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).



SOT−23
CASE 318
STYLE 21

MARKING DIAGRAM & PIN ASSIGNMENT



TR7 = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NTR2101PT1G	SOT−23 (Pb−Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTR2101P

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−8.0			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$				10		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = −6.4 V	T_J = 25°C			−1.0	μA
			T_J = 125°C			−100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±8.0 V				±100	nA
TY CHARACTERISTICS (Note 2)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA		−0.40		−1.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$				2.7		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = −4.5 V, I_D = −3.5 A			39	52	mΩ
		V_{GS} = −2.5 V, I_D = −3.0 A			52	72	
		V_{GS} = −1.8 V, I_D = −2.0 A			79	120	
Forward Transconductance	g_{FS}	V_{GS} = −5.0 V, I_D = −3.5 A			9.0		S
CHARGES AND CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1.0 MHz, V_{DS} = −4.0 V			1173		pF
Output Capacitance	C_{OSS}				289		
Reverse Transfer Capacitance	C_{RSS}				218		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = −4.5 V, V_{DS} = −4.0 V, I_D = −3.5 A			12	15	nC
Gate−to−Source Charge	Q_{GS}				3.8		
Gate−to−Drain Charge	Q_{GD}				2.5		
SWITCHING CHARACTERISTICS (Note 3)							
Turn−On Delay Time	$t_{d(on)}$	V_{GS} = −4.5 V, V_{DD} = −4.0 V, I_D = −1.2 A, R_G = 6.0 Ω			7.4	15	ns
Rise Time	t_r				15.75	25	
Turn−Off Delay Time	$t_{d(off)}$				38	58	
Fall Time	t_f				31	51	
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −1.2 A	T_J = 25°C		−0.73	−1.2	V

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.